

# STPS6100CB(-TR)

## HIGH VOLTAGE POWER SCHOTTKY RECTIFIERS

#### MAIN PRODUCT CHARACTERISTICS

I <sub>F(AV)</sub>	2x3 A
VRRM	100 V
V <sub>F</sub> (max)	0.59 V

#### FEATURES AND BENEFITS

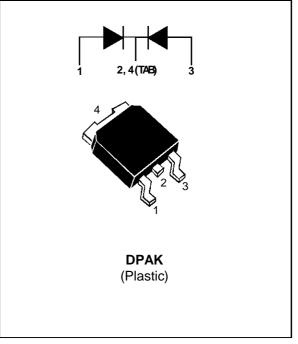
- NEGLIGIBLE SWITCHING LOSSES
- LOW FORWARD DROP VOLTAGE
- LOW CAPACITANCE
- HIGH REVERSE AVALANCHE SURGE CAPABILITY
- TAPE AND REEL OPTION : -TR

#### DESCRIPTION

High voltage dual Schottky rectifier suited for Switch Mode Power Supplies and other Power Converters.

Packaged in DPAK, this device is intended for use in medium voltage operation, and particularly, in high frequency circuitries where low switching losses are required.

### PRELIMINARY DATASHEET



#### **ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter		Value	Unit
V <sub>RRM</sub>	Repetitive Peak Reverse Voltage		100	V
I <sub>F(RMS)</sub>	RMS Forward Current		6	А
I <sub>F(AV)</sub>	Average Forward Current	Tcase = 120°C δ = 0.5	3	A
I <sub>FSM</sub>	Surge Non Repetitive Forward Current	tp = 10 ms Sinusoidal	50	A
I <sub>RRM</sub>	Repetitive Peak Reverse Current	tp =2 μs F = 1KHz	1	A
T <sub>stg</sub>	Storage Temperature Range		- 65 to + 150	°C
Tj	Max. Junction Temperature		125	°C
dV/dt	Critical Rate of Rise of Reverse Voltage		1000	V/µs

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#### THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
R <sub>TH (j-c)</sub>	Junction to Case Thermal Resistance	Per diode	3.5	°C/W
		Total	2	

#### STATIC ELECTRICAL CHARACTERISTICS

Symbol	Tests Conditions	Tests Conditions		Min.	Тур.	Max.	Unit
I <sub>R</sub> *	Reverse leakage Current	Tj = 25°C	V <sub>R</sub> = 100 V			30	μA
		Tj = 125°C			4.5	10	mA
V <sub>F</sub> **	Forward Voltage drop	Tj = 25°C	I <sub>F</sub> = 3 A			0.65	V
		Tj = 125°C	I <sub>F</sub> = 3 A		0.55	0.59	

Pulse test: \* tp = 5 ms, duty cycle < 2 %

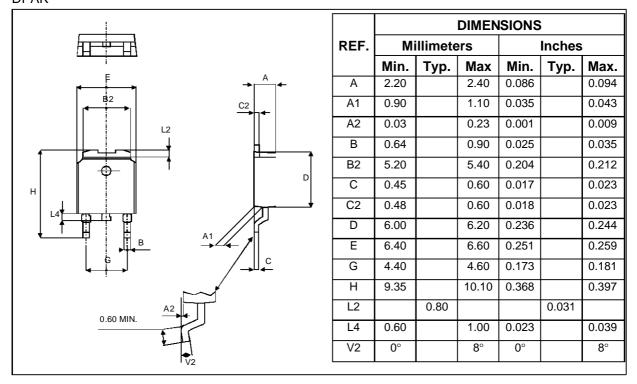
\*\* tp = 380  $\mu$ s, duty cycle < 2%

To evaluate the maximum conduction losses use the following equation :  $\nabla = 1 + 2$ 

 $P = 0.49 \text{ x } I_{F(AV)} + 0.035 I_{F}^{2}(RMS)$ 



#### PACKAGE MECHANICAL DATA DPAK



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